



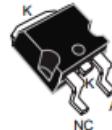
1200V 碳化硅肖特基二极管  
1200V SiC Schottky Diode

# SC20J120BS

## 产品特性 (Feature)

- 零反向恢复电流  
No reverse recovery current
- 正温度系数  
Positive temperature coefficient
- 不受温度影响的开关特性  
Temperature independent switching behavior
- 低压降、高工作温度  
Low forward voltage and high operating temperature
- 优异的浪涌电流能力  
Excellent surge current capability

V <sub>RRM</sub>	1200	V
I <sub>F</sub> , T <sub>C</sub> ≤ 137°C	20	A
Q <sub>C</sub> Typ	126	nC



## 产品优点 (Benefits)

- 降低电磁干扰  
Reduce EMI
- 高功率密度，可用于更高的工作频率  
High power density, enable higher frequency
- 降低散热要求，节约系统成本和尺寸  
Reduce cooling requirements, save system cost and size
- 极大提升系统效率  
Significantly improve system efficiency

## 应用领域 (Applications)

- 光伏逆变器  
Solar inverters
- 功率因数校正  
Power Factor Correction
- 不间断电源  
Uninterruptable power supplies
- 电机驱动  
Motor drives

## 订货型号 (Order Message)

订货型号 Order codes		印记 Marking	封装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen Free-Tube		
SC20J120BS-GE-B	SC20J120BS -GE-BR	SC20J120BS	TO-263-2





## 额定值 Maximum ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	反向重复峰值电压 Repetitive Peak Reverse Voltage	1200	V		
V <sub>RSM</sub>	反向浪涌峰值电压 Surge Peak Reverse Voltage	1200	V		
V <sub>DC</sub>	反向直流电压 DC Blocking Voltage	1200	V		
I <sub>F</sub>	正向平均电流 Continuous Forward Current	20	A	T <sub>C</sub> =150°C	
I <sub>FRM</sub>	正向重复浪涌电流 Repetitive Peak Forward Surge Current	100	A	T <sub>C</sub> =25°C, t <sub>P</sub> =10 ms, Half Sine Wave,	
I <sub>FSM</sub>	正向非重复浪涌电流 Non-Repetitive Peak Forward Surge Current	144	A	T <sub>C</sub> =25°C, t <sub>P</sub> =10ms, Half Sine Wave	
I <sub>F,Max</sub>	正向非重复浪涌电流 Non-Repetitive Peak Forward Surge Current	1200	A	T <sub>C</sub> =25°C, t <sub>P</sub> = 10 μs, Pulse	
T <sub>J</sub> , T <sub>stg</sub>	工作温度和存储温度 Operating Junction and Storage Temperature	-55 to +175	°C		

## 电学特性(单管芯) Electrical Characteristics, (Per Leg)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	正向电压 Forward Voltage	1.5 2.2	1.8 3.0	V	I <sub>F</sub> = 20 A T <sub>J</sub> =25°C I <sub>F</sub> = 20 A T <sub>J</sub> =175°C	Fig. 1
I <sub>R</sub>	反向电流 Reverse Current	15 65	100 300	μA	V <sub>R</sub> = 1200 V T <sub>J</sub> =25°C V <sub>R</sub> = 1200 V T <sub>J</sub> =175°C	Fig. 2
Q <sub>C</sub>	总储存电荷 Total Capacitive Charge	126		nC	V <sub>R</sub> = 800V, T <sub>J</sub> = 25°C Q <sub>C</sub> = $\int_0^{V_R} C(V)dV$	Fig. 4
C	总电容 Total Capacitance	1702 120 95		pF	V <sub>R</sub> = 0 V, T <sub>J</sub> = 25°C, f = 1 MHz V <sub>R</sub> = 400 V, T <sub>J</sub> = 25°C, f = 1 MHz V <sub>R</sub> = 800 V, T <sub>J</sub> = 25°C, f = 1 MHz	Fig. 3
E <sub>C</sub>	电容储存能量 Capacitance Stored Energy	32.5		μJ	V <sub>R</sub> = 600 V	Fig. 5

## 热性能(Thermal Characteristics)

Symbol	Parameter	Typ.	Unit	Note
R <sub>θJC</sub>	Thermal Resistance from Junction to Case	0.68	°C/W	



## 性能曲线图 Performance curve

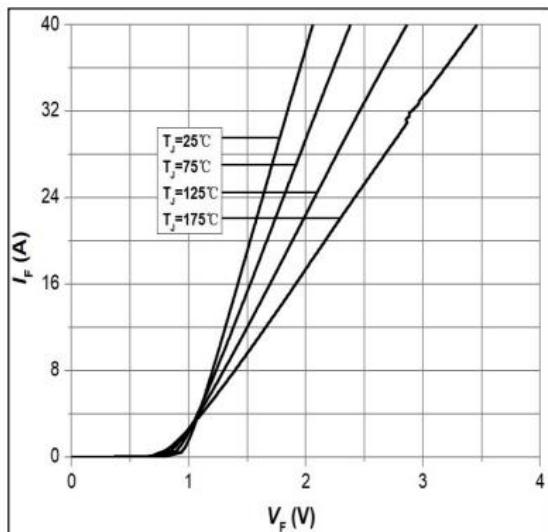


Figure 1. Forward Characteristics

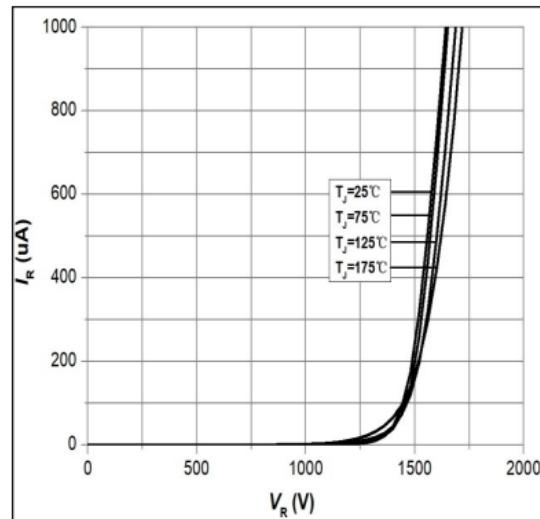


Figure 2. Reverse Characteristics

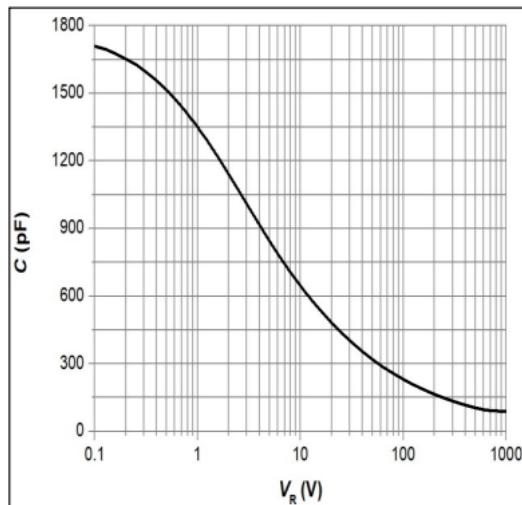


Figure 3. Capacitance vs. Reverse Voltage

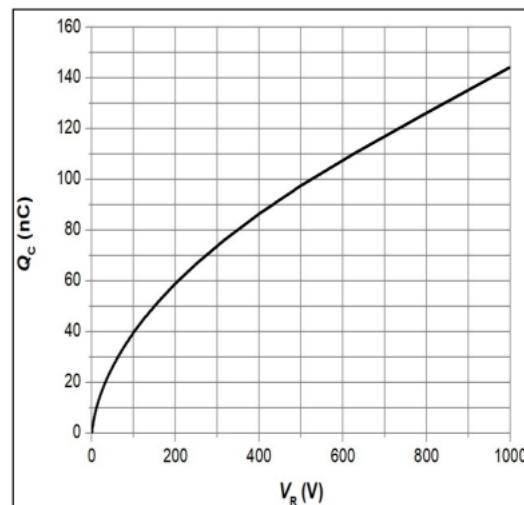


Figure 4. Capacitance Charge vs. Reverse Voltage

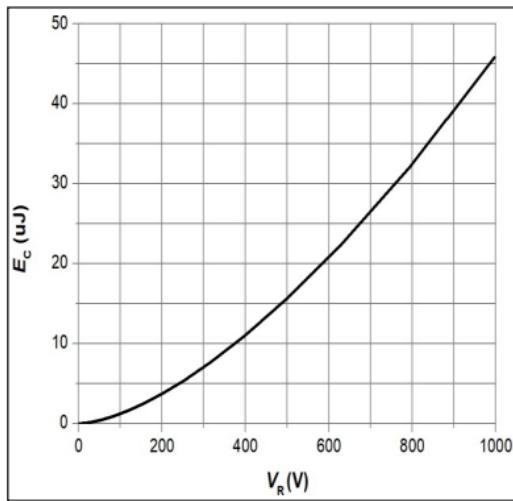
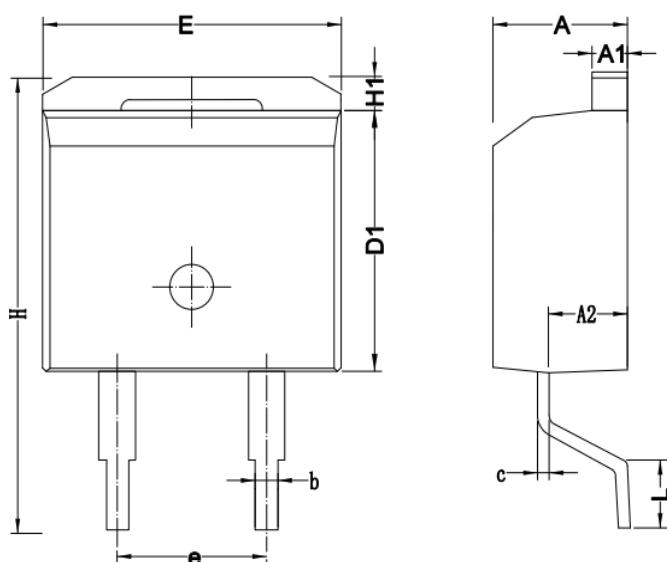


Figure 5. Capacitance Stored Energy



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Package Dimensions: TO-263-2

SYMBOL	MM	
	MIN	MAX
A	4.18	4.68
A1	1.10	1.50
A2	2.40	2.80
b	0.63	1.00
c	0.35	0.70
D1	8.80	9.40
E	9.88	10.48
e	5.08 BSC	
H	14.50	16.50
H1	0.95	1.45
L	1.70	2.70

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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
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SC20J120BS

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